

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI AVD004P** is Designed for

FEATURES:

-
-
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	650 mA PEAK
V_{CB}	32 V
P_{DISS}	18 W PEAK
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	5.0 °C/W

PACKAGE STYLE .280 4L PILL(A)

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.095 / 2.41	.105 / 2.67
B	.195 / 4.95	.205 / 5.21
C	1.000 / 25.40	
D	.004 / 0.10	.007 / 0.18
E	.050 / 1.27	.065 / 1.65
F		.145 / 3.68
G	.275 / 6.99	.285 / 7.21

ORDER CODE: ASI10555

CHARACTERISTICS $T_C = 25\text{ }^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 1 mA	45			V
BV_{CER}	I _C = 5 mA R _{BE} = 10 Ω	45			V
BV_{EBO}	I _E = 1 mA	3.5			V
I_{CES}	V _{CE} = 28 V			1.0	mA
h_{FE}	V _{CE} = 5.0 V I _C = 200 mA	30		300	---
P_G	V _{CC} = 28 V P _{OUT} = 4.0 W f = 1025 - 1150	9.0			dB
η_C	MHZ	35			%